

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-13. (Canceled)

14. (Currently Amended) A luminescent device comprising:
a thin film transistor provided over an insulating surface;
a luminescent element electrically connected with said thin film transistor,
comprising:
an organic compound layer containing an alkaline metal;
an anode; and
a cathode; and
at least one insulating layer provided between said thin film transistor and said
luminescent element,
wherein said insulating layer is capable of ~~adsorbing~~ absorbing said alkaline
metal.

15. (Previously Presented) A luminescent device according to claim 14, wherein
said at least one insulating layer comprises a silicon nitride film containing fluorine at a
concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

16. (Previously Presented) A luminescent device according to claim 14, wherein
said at least one insulating layer comprises an organic resin film containing a particle
comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

17. (Previously Presented) A luminescent device according to claim 14, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

18. (Previously Presented) A luminescent device according to claim 14, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

19. (Withdrawn - Currently Amended) A luminescent device comprising:
a thin film transistor provided over an insulating surface;
a luminescent element electrically connected with said thin film transistor,
comprising:
 an organic compound layer;
 an anode;
 a buffer layer containing an alkaline metal; and
 a cathode; and
at least one insulating layer provided between said thin film transistor and said luminescent element,
wherein said insulating layer is capable of ~~adsorbing~~ absorbing said alkaline metal.

20. (Withdrawn) A device according to claim 19, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

21. (Withdrawn) A device according to claim 19, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

22. (Withdrawn) A device according to claim 19, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

23. (Withdrawn) A device according to claim 19, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

24. (Withdrawn - Currently Amended) A luminescent device comprising:
a thin film transistor provided over an insulating surface;
a luminescent element electrically connected with said thin film transistor,
comprising:
 an organic compound layer;
 an anode; and
 a cathode containing an alkaline-earth metal; and
at least one insulating layer provided between said thin film transistor and said luminescent element,
wherein said insulating layer is capable of ~~adsorbing~~ absorbing said alkaline-earth metal.

25. (Withdrawn) A device according to claim 24, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

26. (Withdrawn) A device according to claim 24, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

27. (Withdrawn) A device according to claim 24, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

28. (Withdrawn) A device according to claim 24, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

29. (Withdrawn - Currently Amended) A luminescent device comprising:
a thin film transistor provided over an insulating surface;
a luminescent element electrically connected with said thin film transistor,
comprising:

an organic compound layer containing an alkaline-earth metal;

an anode; and

a cathode; and

at least one insulating layer provided between said thin film transistor and said luminescent element,

wherein said insulating layer is capable of ~~adsorbing~~ absorbing said alkaline-earth metal.

30. (Withdrawn) A device according to claim 29, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

31. (Withdrawn) A device according to claim 29, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

32. (Withdrawn) A device according to claim 29, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

33. (Withdrawn) A device according to claim 29, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

34. (Withdrawn - Currently Amended) A luminescent device comprising:
a thin film transistor provided over an insulating surface of a substrate;
a luminescent element electrically connected with said thin film transistor,
comprising:
 an organic compound layer;
 an anode;
 a buffer layer containing an alkaline-earth metal; and
 a cathode; and
at least one insulating layer provided between said thin film transistor and said luminescent element

wherein said insulating layer is capable of ~~adsorbing~~ absorbing said alkaline-earth metal.

35. (Withdrawn) A device according to claim 34, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

36. (Withdrawn) A device according to claim 34, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

37. (Withdrawn) A device according to claim 34, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

38. (Withdrawn) A device according to claim 34, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

39. (Currently Amended) A luminescent device comprising:
a thin film transistor provided over an insulating surface;
a luminescent element electrically connected with said thin film transistor,
comprising:
an organic compound layer containing an alkaline metal;
an anode; and
a cathode; and

at least one insulating layer provided between said thin film transistor and said luminescent element,

wherein said insulating layer is capable of ~~adsorbing~~ absorbing said alkaline metal, and

wherein said organic compound layer comprises a hole implantation layer.

40. (Previously Presented) A luminescent device according to claim 39, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

41. (Previously Presented) A luminescent device according to claim 39, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

42. (Previously Presented) A luminescent device according to claim 39, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

43. (Previously Presented) A luminescent device according to claim 39, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

44.-48. (Canceled)

49. (Currently Amended) A luminescent device comprising:
a thin film transistor provided over an insulating surface;

a luminescent element electrically connected with said thin film transistor, comprising:

an organic compound layer containing an alkaline metal and an inorganic material;

an anode; and

a cathode; and

at least one insulating layer provided between said thin film transistor and said luminescent element,

wherein said insulating layer is capable of ~~adsorbing~~ absorbing said alkaline metal.

50. (Previously Presented) A luminescent device according to claim 49, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

51. (Previously Presented) A luminescent device according to claim 49, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

52. (Previously Presented) A luminescent device according to claim 49, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

53. (Previously Presented) A luminescent device according to claim 49, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

54. (Currently Amended) A luminescent device comprising:
a thin film transistor provided over an insulating surface;
a luminescent element electrically connected with said thin film transistor,
comprising:
an organic compound layer containing an alkaline metal and an inorganic
material;
an anode; and
a cathode; and
at least one insulating layer provided between said thin film transistor and said
luminescent element,
wherein said insulating layer is capable of ~~adsorbing~~ absorbing said alkaline
metal, and
wherein said organic compound layer comprises a hole implantation layer.

55. (Previously Presented) A luminescent device according to claim 54, wherein
said at least one insulating layer comprises a silicon nitride film containing fluorine at a
concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

56. (Previously Presented) A luminescent device according to claim 54, wherein
said at least one insulating layer comprises an organic resin film containing a particle
comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

57. (Previously Presented) A luminescent device according to claim 54, wherein
said at least one insulating layer comprises a laminated layer of a silicon nitride film
containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more and an organic resin film
containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or
indium (In) compound.

58. (Previously Presented) A luminescent device according to claim 54, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.